

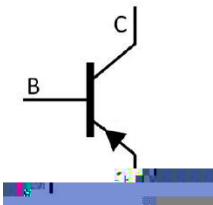
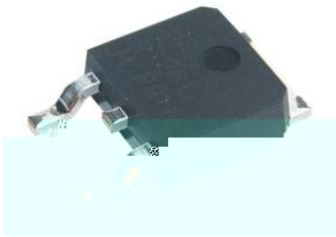
/ Descriptions

WR0585 M M E SQS æ M y s ll 1 Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

High breakdown voltage, adoption of MBIT process excellent h_{FE} linearity

High voltage driver applications.

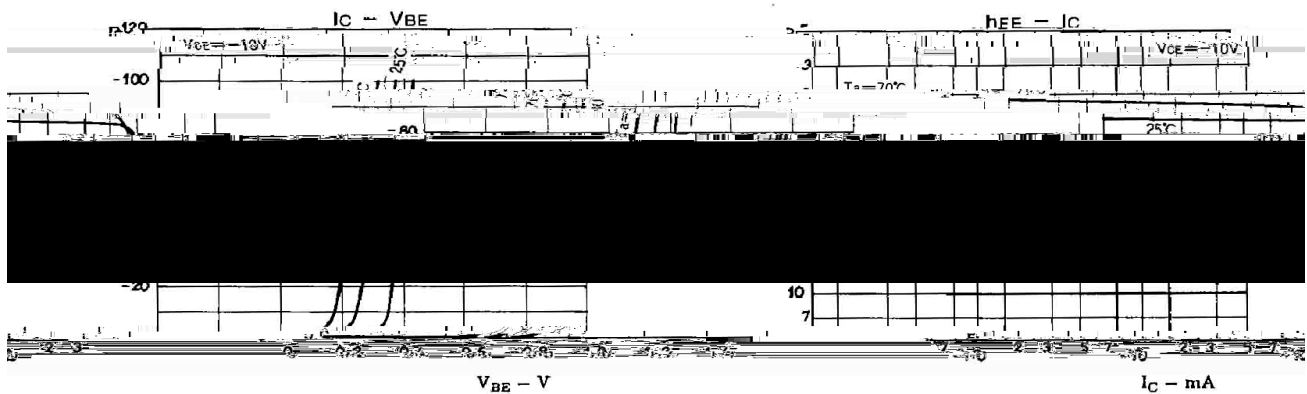
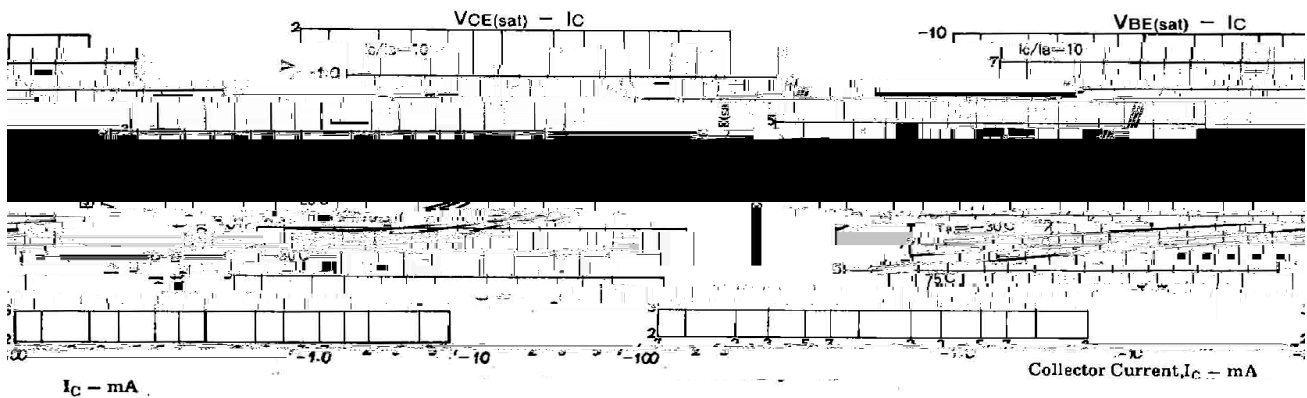
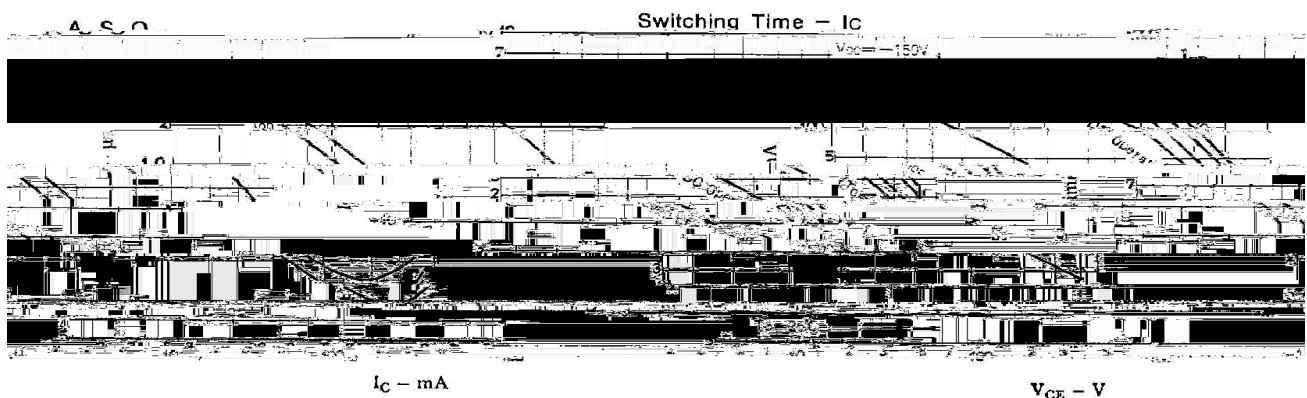


PIN1 χ Base PIN 2,4 χ Collector PIN 3 χ Emitter

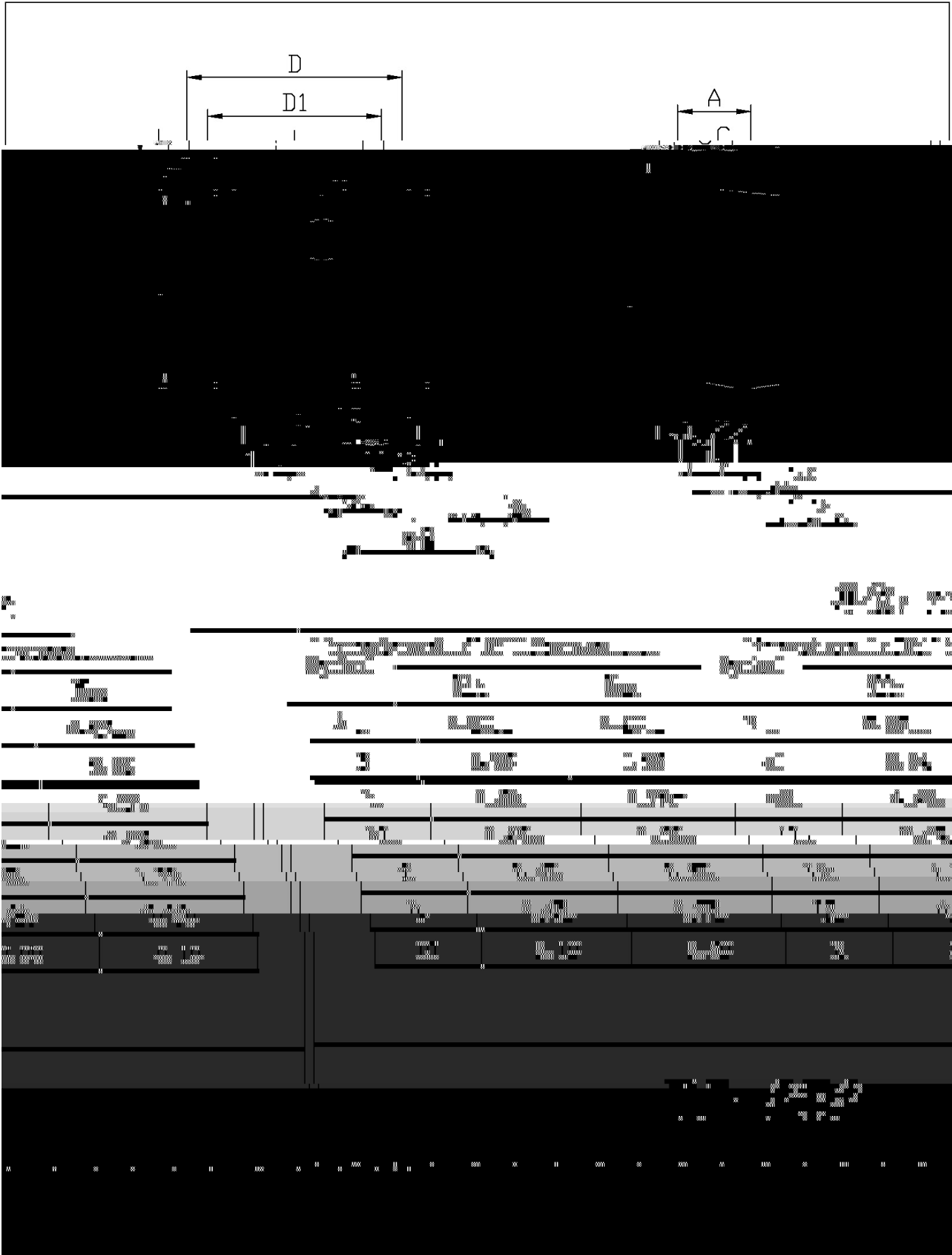
/ h_{FE} Classifications & Marking

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-400	V

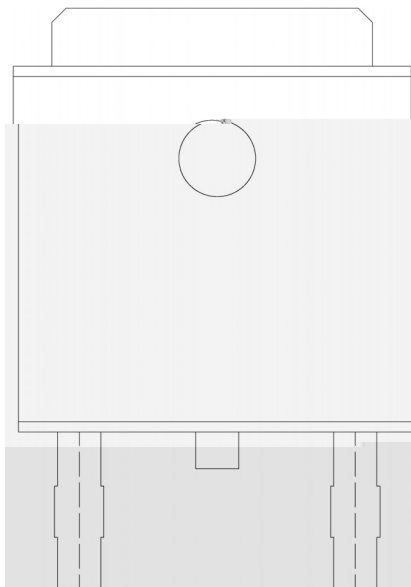
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



б " X

BR X 蓝箭公司

A1700 X 2SA1700

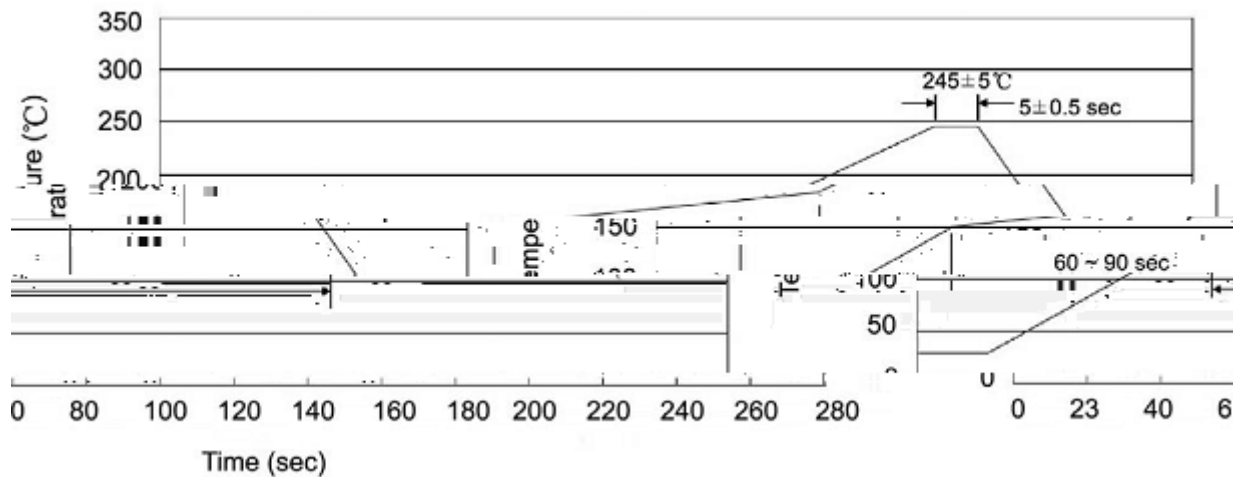
D= 放大倍数

---- X 放大倍数 放大倍数

Note:

BR: A13()Tj20mpawEFO

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明

1. 预加热: 25~150 °C, Time: 60~90sec;
2. 峰值温度: 245±5 °C, Time: 5±0.5sec;
3. 冷却速度: 2~10 °C/sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 245±5 °C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

测试条件: 260±5 °C, Time: 10±1 sec. Temp.: 260±5 Time: 10±1 sec

/ Packaging SPEC.

包装形式: REEL

Package Type	Units	Dimension	(unit mm ³)
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